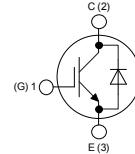


**XPT IGBT**

Copack

**I<sub>C25</sub>** = **9 A**  
**V<sub>CES</sub>** = **1200 V**  
**V<sub>CE(sat)typ</sub>** = **1.8 V**

**Part number****IXA4IF1200UC****Features / Advantages:**

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
  - short circuit rated for 10  $\mu$ sec.
  - very low gate charge
  - low EMI
  - square RBSOA @ 3x I<sub>c</sub>
- Thin wafer technology combined with the XPT design results in a competitive low V<sub>CE(sat)</sub>
- SONIC™ diode
  - fast and soft reverse recovery
  - low operating forward voltage

**Applications:**

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers

**Package:**

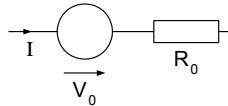
- Housing: TO-252 (DPak)
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

**IGBT****Ratings**

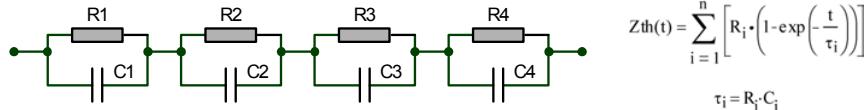
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V <sub>CES</sub>	Collector emitter voltage	V <sub>GE</sub> = 0 V	T <sub>VJ</sub> = 25°C		1200	V	
V <sub>GES</sub>	Maximum DC gate voltage		T <sub>VJ</sub> = 25°C		$\pm 20$	V	
I <sub>C25</sub>	Collector current		T <sub>C</sub> = 25°C		9	A	
I <sub>C100</sub>			T <sub>C</sub> = 100°C		5	A	
P <sub>tot</sub>	Total power dissipation		T <sub>VJ</sub> = 25°C		45	W	
I <sub>CES</sub>	Collector emitter leakage current	V <sub>CE</sub> = V <sub>CES</sub> ; V <sub>GE</sub> = 0 V	T <sub>VJ</sub> = 25°C	0.1	0.1	mA	
			T <sub>VJ</sub> = 125°C		0.1	mA	
I <sub>GES</sub>	Gate emitter leakage current	V <sub>CE</sub> = 0 V; V <sub>GE</sub> = $\pm 20$ V			500	nA	
V <sub>CE(sat)</sub>	Collector emitter saturation voltage	I <sub>C</sub> = 3 A; V <sub>GE</sub> = 15 V	T <sub>VJ</sub> = 25°C	1.8	2.1	V	
			T <sub>VJ</sub> = 125°C		2.1	V	
V <sub>GE(th)</sub>	Gate emitter threshold voltage	I <sub>C</sub> = 0.1 mA; V <sub>GE</sub> = V <sub>CE</sub>		5.4	6	6.5	V
I <sub>Gon</sub>	Total gate charge	V <sub>CE</sub> = 600 V; V <sub>GE</sub> = 15 V; I <sub>C</sub> = 3 A		12		nC	
t <sub>d(on)</sub>	Turn-on delay time				70	ns	
t <sub>r</sub>	Current rise time				40	ns	
t <sub>d(off)</sub>	Turn-off delay time	Inductive load			250	ns	
t <sub>f</sub>	Current fall time	V <sub>CE</sub> = 600 V; I <sub>C</sub> = 3 A			100	ns	
E <sub>on</sub>	Turn-on energy per pulse	V <sub>GE</sub> = $\pm 15$ V; R <sub>G</sub> = 330 $\Omega$	T <sub>VJ</sub> = 125°C	0.4		mJ	
E <sub>off</sub>	Turn-off energy per pulse				0.3	mJ	
RBSOA	Reverse bias safe operation area	V <sub>GE</sub> = 15 V; R <sub>G</sub> = 330 $\Omega$ V <sub>CEK</sub> = 1200 V	T <sub>VJ</sub> = 125°C		9	A	
SCSOA	Short circuit safe operation area						
t <sub>sc</sub>	Short circuit duration	V <sub>CE</sub> = 900 V; V <sub>GE</sub> = $\pm 15$ V	T <sub>VJ</sub> = 125°C		10	$\mu$ s	
I <sub>sc</sub>	Short circuit current	R <sub>G</sub> = 330 $\Omega$ ; non-repetitive			12	A	
R <sub>thJC</sub>	Thermal resistance junction to case				2.7	K/W	

**Diode**

Symbol	Definition	Conditions	Ratings		
			min.	typ.	max.
$I_{F25}$	Forward current	$T_C = 25^\circ C$			10 A
$I_{F100}$		$T_C = 100^\circ C$			6 A
$V_F$	Forward voltage	$I_F = 3 A$	$T_{VJ} = 25^\circ C$	1.9	2.2 V
			$T_{VJ} = 125^\circ C$	1.9	V
$Q_{rr}$	Reverse recovery charge	$V_R = 600 V$		0.5	$\mu C$
$I_{RM}$	Maximum reverse recovery current	$V_R = 600 V$		5 A	
$t_{rr}$	Reverse recovery time	$di_F/dt = -150 A/\mu s$	$T_{VJ} = 125^\circ C$	350 ns	
$E_{rec(off)}$	Reverse recovery losses at turn-off	$I_F = 3 A$		0.1 mJ	
$R_{thJC}$	Thermal resistance junction to case			3 K/W	

**Equivalent Circuits for Simulation**

Symbol	Definition	Ratings		
		min.	typ.	max.
$V_0$	IGBT			1.1 V
$R_0$				460 mΩ
$V_0$	Diode			1.25 V
$R_0$				280 mΩ

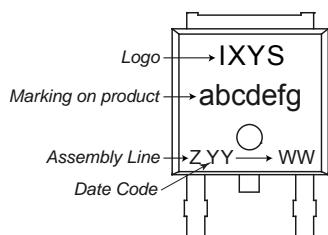


	IGBT	Diode
$R_1$	tbd	tbd
$R_2$	tbd	tbd
$R_3$	tbd	tbd
$R_4$	tbd	tbd
$\tau_1$	tbd	tbd
$\tau_2$	tbd	tbd
$\tau_3$	tbd	tbd
$\tau_4$	tbd	tbd

## Package TO-252 (DPak)

Ratings			
Symbol	Definition	Conditions	
			min.
T <sub>vJ</sub>	Virtual junction temperature		-55
T <sub>stg</sub>	Storage temperature		-55
R <sub>thCH</sub>	Thermal resistance case to heatsink		0.50
Weight			0.3
F <sub>c</sub>	Mounting force with clip		20
			60
			N

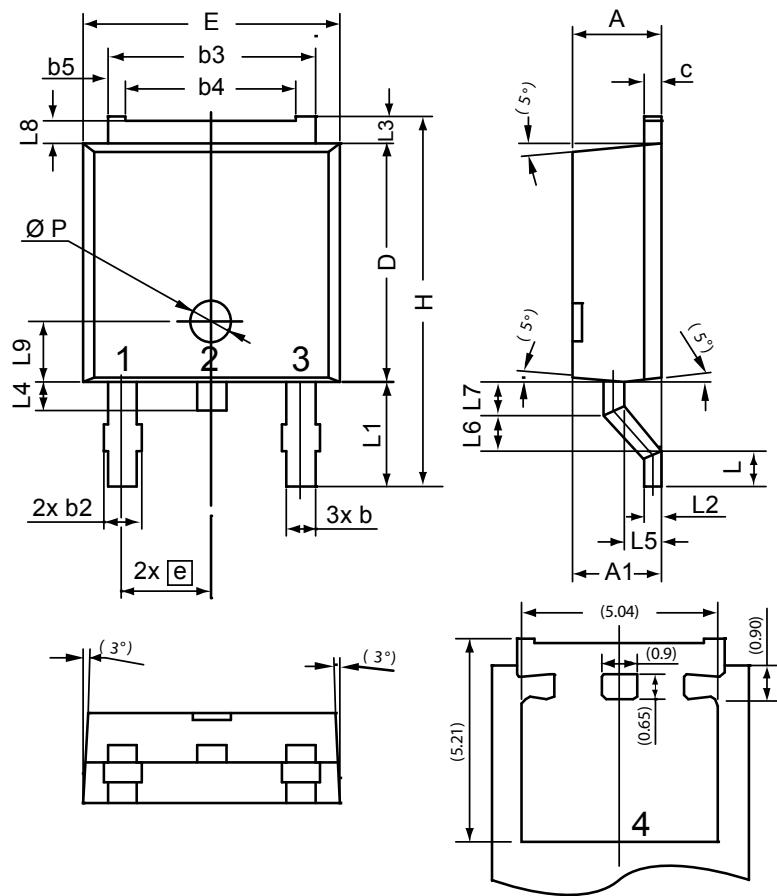
## Product Marking



## Part number

I = IGBT  
 X = XPT IGBT  
 A = Gen 1 / std  
 4 = Current Rating [A]  
 IF = Copack  
 1200 = Reverse Voltage [V]  
 UC = TO-252AA (DPak)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	IXA 4 IF 1200 UC	IXA4IF1200UC	Tape & Reel	2500	510217



Dim.	Millimeters		Inches	
	min	max	min	max
A	2.20	2.40	0.087	0.094
A1	2.10	2.50	0.083	0.098
b	0.66	0.86	0.026	0.034
b2	-	0.96	-	0.038
b3	5.04	5.64	0.198	0.222
b4	4.34 BSC		0.171 BSC	
b5	0.50 BSC		0.020 BSC	
c	0.40	0.60	0.016	0.024
D	5.90	6.30	0.232	0.248
E	6.40	6.80	0.252	0.268
e	2.10	2.50	0.083	0.098
H	9.20	9.80	0.362	0.386
L	0.55	1.02	0.022	0.040
L1	2.50	2.90	0.098	0.114
L2	0.40	0.60	0.016	0.024
L3	0.50	0.90	0.020	0.035
L4	0.60	1.00	0.024	0.039
L5	0.82	1.22	0.032	0.048
L6	0.79	0.99	0.031	0.039
L7	0.81	1.01	0.032	0.040
L8	0.40	0.80	0.016	0.031
L9	1.50 BSC		0.059 BSC	
Ø P	1.00 BSC		0.039 BSC	



